2SC2620

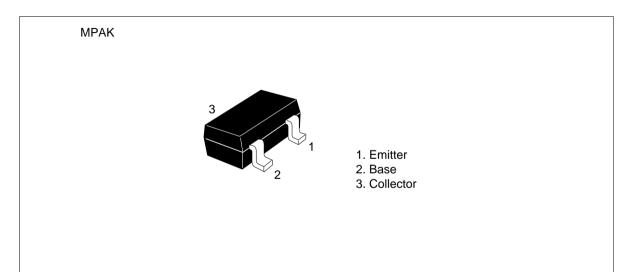
Silicon NPN Epitaxial Planar

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Application

VHF amplifier, Local oscillator

Outline





2SC2620

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol		Unit	
Collector to base voltage	V _{CBO}	30	V	
Collector to emitter voltage	V _{CEO}	20	V	
Emitter to base voltage	V _{EBO}	4	V	
Collector current	Ι _c	20	mA	
Collector power dissipation	Pc	100	mW	
Junction temperature	Тј	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Electrical Characteristics ($Ta = 25^{\circ}C$)

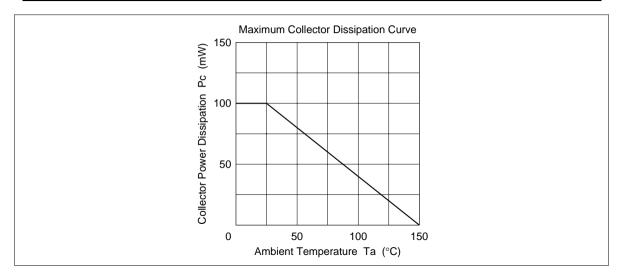
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	30	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	20	_	_	V	$I_c = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	_	_	V	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	μΑ	$V_{\rm CB} = 10 \text{ V}, I_{\rm C} = 0$
Emitter cutoff current	I _{EBO}	_	_	0.5	μΑ	$V_{EB} = 2 V, I_{C} = 0$
DC current transfer ratio	h_{FE}^{*1}	60	—	200		$V_{ce} = 6 V, I_c = 1 mA$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	0.17	_	V	$I_{c} = 20 \text{ mA}, I_{B} = 4 \text{ mA}$
Base to emitter voltage	V_{BE}	_	0.72	_	V	V_{ce} = 6 mA, I_c = 1 mA
Gain bandwidth product	f _T	_	940	_	MHz	$V_{ce} = 6 \text{ V}, \text{ I}_{c} = 5 \text{ mA}$
Collector output capacitance	Cob	—	0.9	_	pF	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$
Note: 1. The 2SC2620 is grouped by h_{FE} as follows.						
Grade B C						

Grade	В	С
Mark	QB	QC
h _{FE}	60 to 120	100 to 200

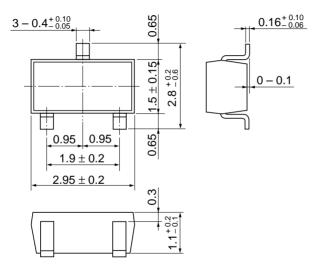
See characteristic curves of 2SC535.

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2SC2620



Unit: mm



Hitachi Code	MPAK
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.011 g

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